



The ZM098N06H



$T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	20	V
Continuous Drain Current	$I_{D@TC=25}$	55	A
	$I_{D@TC=75}$	42	A
	$I_{D@TC=100}$	35	A
Pulsed Drain Current	I_{DM}	104	A
Total Power Dissipation($TC=25$)	$P_D@TC=25$	120	W
Total Power Dissipation($TA=25$)	$P_D@TA=25$	5	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy@ $L=0.1mH$	E_{AS}	80	mJ



Fig.1 SOA Maximum Safe Operating Area

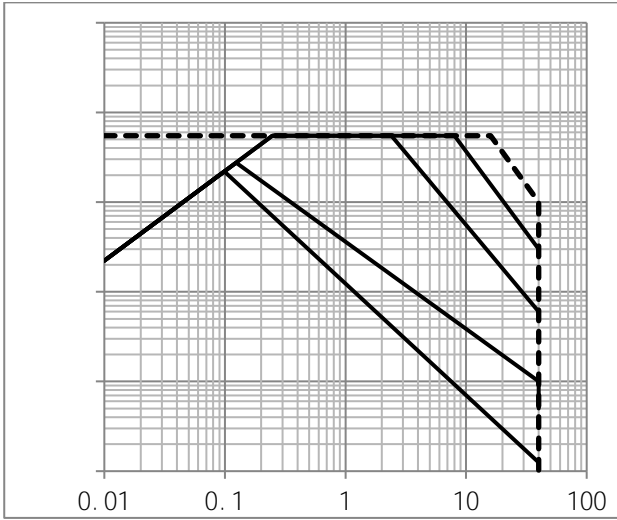


Fig.2 ID-Junction Temperature

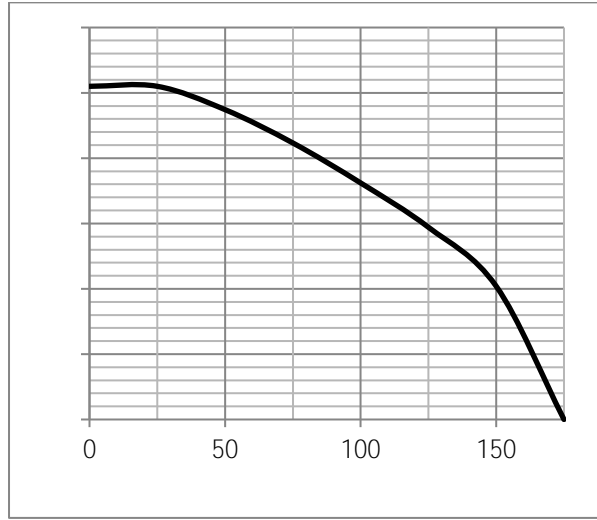


Fig.3 Gate-Charge Characteristics

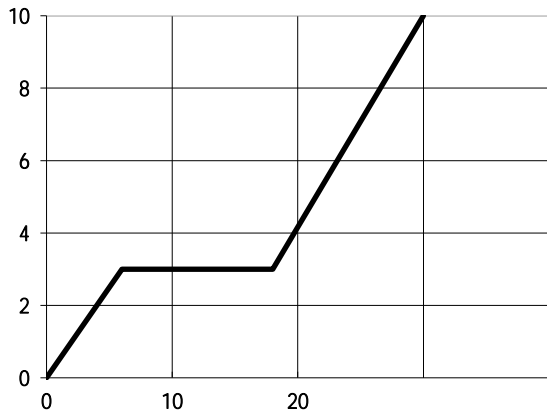


Fig.4 Capacitance Characteristics

Fig.5 Power Dissipation

Fig.6 Typical output Characteristics



Fig.7 Threshold Voltage V.S Junction Temperature Fig.8 Resistance V.S Drain Current

Fig.9 On-Resistance VS Gate Source Voltage

Fig.10 On-Resistance V.S Junction Temperature

Fig.11



Fig.13 Switching Time Measurement Circuit

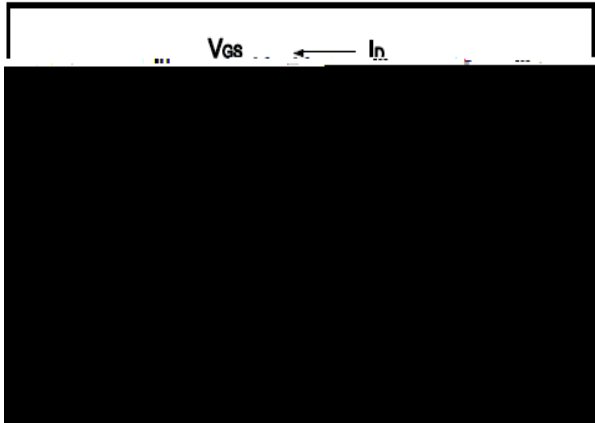


Fig.14 Gate Charge Waveform

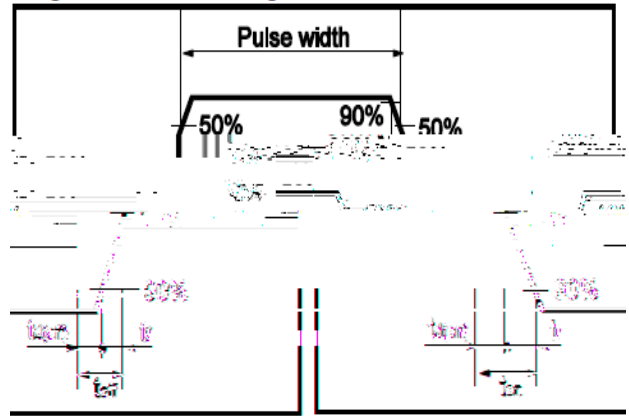


Fig.15 Avalanche Measurement Circuit

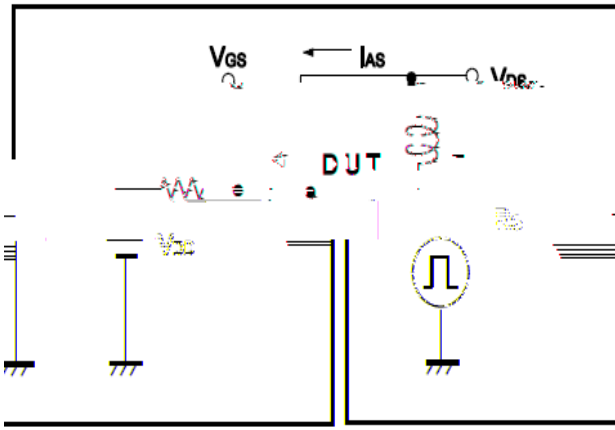


Fig.16 Avalanche Waveform



Dimensions (TO-220)

Unit mm

	2..		2
	0.		.			0 2	
	..		2.		.		2
	.		..		0 .		2 .
	. 1		.		1..	1 .	2..
	..		.		0 .		1..
	.		.		0..		